

**ZXGD3103N8**
**SYNCHRONOUS MOSFET CONTROLLER**
**Description**

The ZXGD3103 is intended to drive MOSFETs configured as ideal diode replacements. The device is comprised of a differential amplifier detector stage and high current driver. The detector monitors the reverse voltage of the MOSFET such that if body diode conduction occurs a positive voltage is applied to the MOSFET's Gate pin.

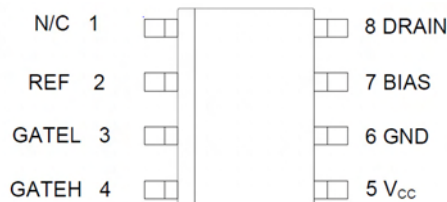
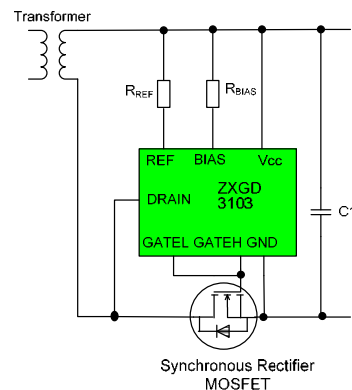
Once the positive voltage is applied to the Gate the MOSFET switches on allowing reverse current flow. The detectors' output voltage is then proportional to the MOSFET Drain-Source reverse voltage drop and this is applied to the Gate via the driver. This action provides a rapid turn off as current decays.

**Features**

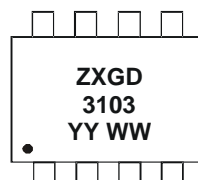
- Proportional Gate Drive
- Turn-off propagation delay 15ns and turn-off time 20ns.
- Detector threshold voltage ~10mV
- Standby current 5mA
- Suitable for Discontinuous Mode (DCM), Critical Conduction Mode (CrCM) and Continuous Mode (CCM) operation
- 5-15V  $V_{CC}$  range

**Applications**

- Flyback Converters in:
  - Adaptors
  - LCD Monitors
  - Server PSU's
  - Set Top Boxes
  - LCD TV
- Resonant Converters
- LED TV
- High power Adaptors
- Street Lighting
- ATX psu

**Pin out details**

**SO-8**
**Typical Configuration**

**Ordering information**

Device	Status	Package	Part Mark	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXGD3103N8TC	Production	SO8	ZXGD3103	13	12	2500

**Marking information**


ZXGD = Product Type Marking Code, Line 1  
 3103 = Product Type Marking Code, Line 2  
 YY = Year (ex: 11 = 2011)  
 WW = Week (01 - 53)

### Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Supply voltage <sup>1</sup>	$V_{CC}$	15	V
Continuous Drain pin voltage <sup>1</sup>	$V_D$	-3 to 180	V
GATEH and GATEL output Voltage <sup>1</sup>	$V_G$	-3 to $V_{CC} + 3$	V
Driver peak source current	$I_{SOURCE}$	2.5	A
Driver peak sink current	$I_{SINK}$	6	A
Reference current	$I_{REF}$	25	mA
Bias voltage	$V_{BIAS}$	$V_{CC}$	V
Bias current	$I_{BIAS}$	100	mA
Power dissipation at $T_A = 25^\circ\text{C}$	$P_D$	490	mW
Operating junction temperature	$T_j$	-40 to +150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-50 to +150	$^\circ\text{C}$

Notes: 1. All voltages are relative to GND pin.

### Thermal resistance

Parameter	Symbol	Value	Unit
Junction to ambient (a)	$R_{\theta JA}$	255	$^\circ\text{C/W}$
Junction to lead (b)	$R_{\theta LA}$	120	$^\circ\text{C/W}$

Notes: a. Mounted on minimum 1oz weight copper on FR4 PCB in still air conditions.  
b. Output Drivers - Junction to solder point at end of the lead 5 and 6

### ESD Rating

Model	Rating	Unit
Human Body	2000	V
Machine	300	V

**ZXGD3103N8**

 Electrical characteristics at  $T_A = 25^\circ\text{C}$ ;  $V_{CC} = 10\text{V}$ ;  $R_{BIAS} = 3.3\text{k}\Omega$ ;  $R_{REF} = 4.3\text{k}\Omega$ 

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Input and supply characteristics						
Operating current	I <sub>OP</sub>	V <sub>D</sub> ≤ -200m V	-	2.16	-	mA
		V <sub>D</sub> ≥ 0V	-	5.16	-	
Gate Driver						
Turn-off Threshold Voltage(**)	V <sub>T</sub>	V <sub>G</sub> = 1V, ( * )	-16	-10	0	mV
GATE output voltage ( ** )	V <sub>G(off)</sub>	V <sub>D</sub> ≥ 0V, ( * )	-	0.73	1	V
	V <sub>G</sub>	V <sub>D</sub> = -50mV, ( † )	6.0	7.2	-	
		V <sub>D</sub> = -100mV, ( † )	8.8	9.2	-	
		V <sub>D</sub> ≤ -150mV, ( † )	9.2	9.4	-	
		V <sub>D</sub> ≤ -200mV, ( † )	9.3	9.5	-	

 Switching performance (") for  $Q_{G(tot)} = 82\text{nC}$ 

Turn on Propagation delay	$t_{d1}$	Refer to switching waveforms in Fig. 3		150		ns
Turn off Propagation delay	$t_{d2}$			15		
Gate rise time	$t_r$			450		
Gate fall time	$t_f$	Continuous Conduction Mode		21		
		Discontinuous Conduction Mode		17		

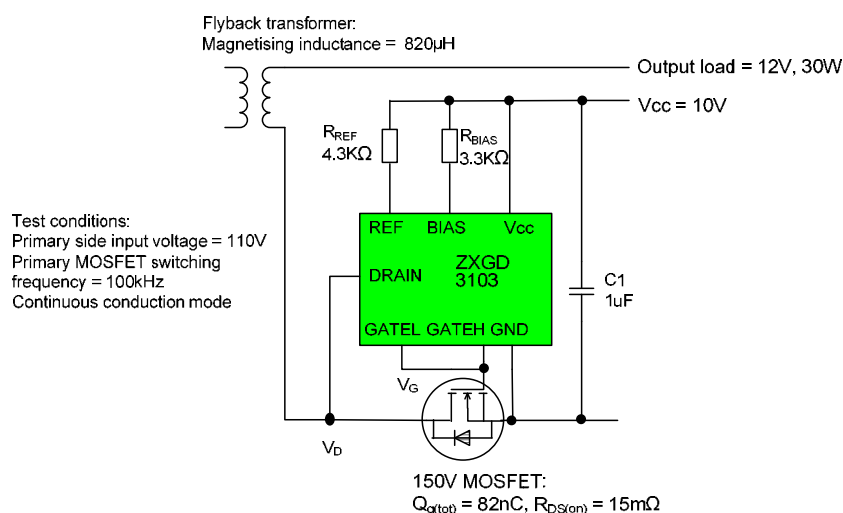
**Notes:**

(\*\*) GATEH connected to GATEL

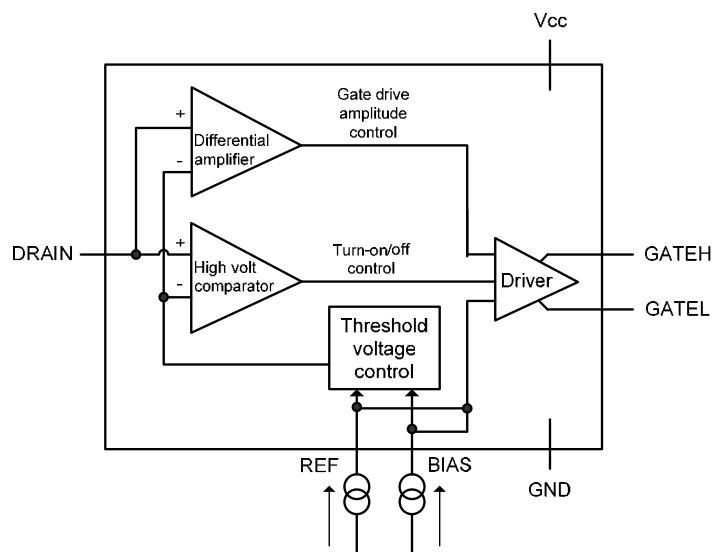
 (\*)  $R_H = 100\text{k}\Omega$ ,  $R_L = \text{O/C}$ 

 (†)  $R_L = 100\text{k}\Omega$ ,  $R_H = \text{O/C}$ 

(") refer to test circuit below

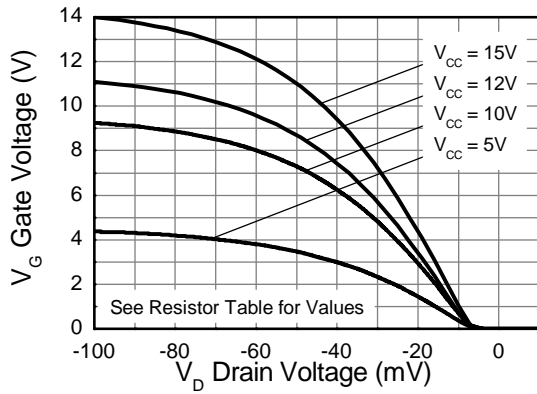


## Schematic Symbol and Pin Out Details

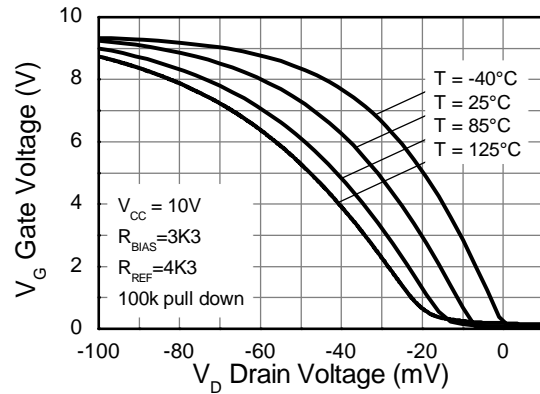


Pin No.	Name	Description and function
1	NC	<b>No Internal connection</b>
2	REF	<b>Reference</b> This pin is connected to $V_{CC}$ via resistor, $R_{REF}$ .
3	GATEL	<b>Gate turn off</b> This pin sinks current, $I_{SINK}$ , from the synchronous MOSFET Gate.
4	GATEH	<b>Gate turn on</b> This pin sources current, $I_{SOURCE}$ , to the synchronous MOSFET Gate.
5	$V_{CC}$	<b>Power Supply</b> This is the supply pin. It is recommended to decouple this point to ground closely with a ceramic capacitor.
6	GND	<b>Ground</b> This is the ground reference point. Connect to the synchronous MOSFET Source terminal.
7	BIAS	<b>Bias</b> This pin is connected to $V_{CC}$ via resistor, $R_{BIAS}$ .
8	DRAIN	<b>Drain connection</b> This pin connects directly to the synchronous MOSFET Drain terminal.

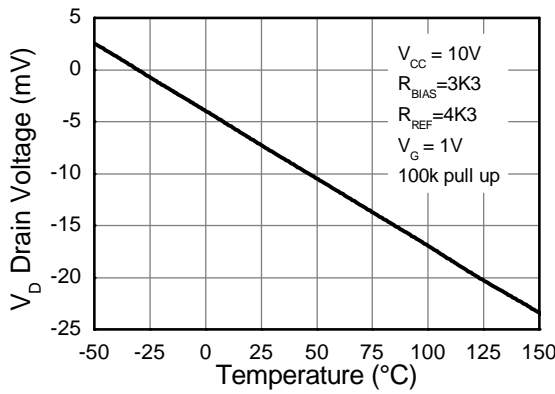
## Typical Characteristics



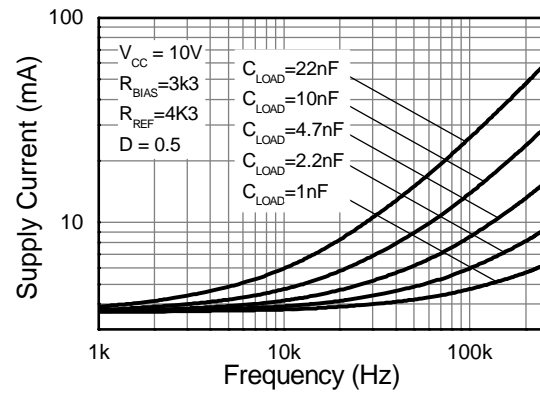
Transfer Characteristic



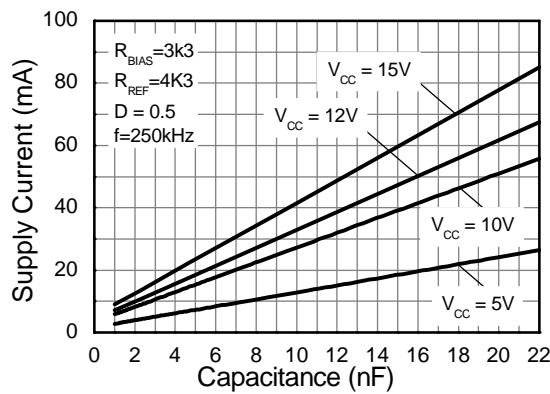
Transfer Characteristic



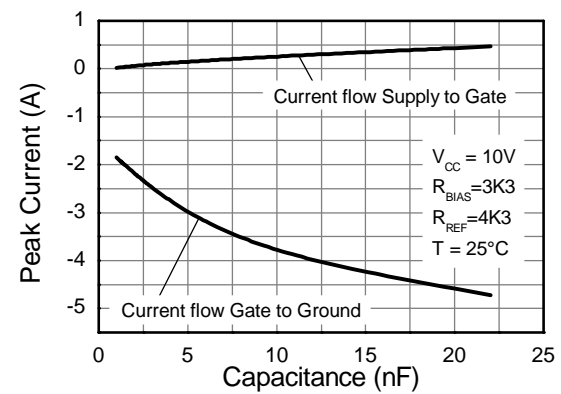
Drain Sense Voltage vs Temperature



Supply Current vs Frequency

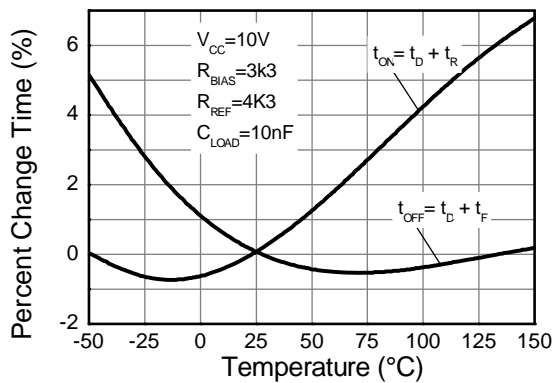
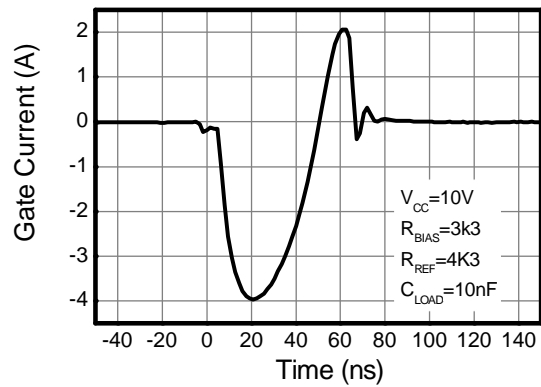
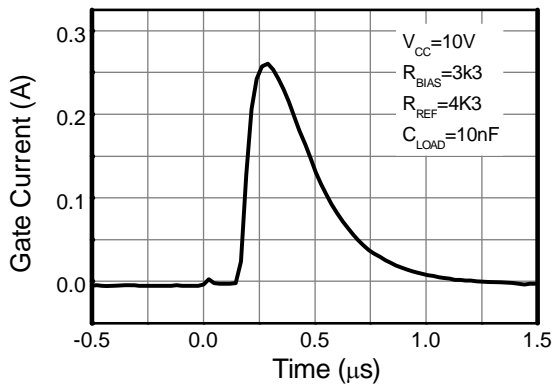
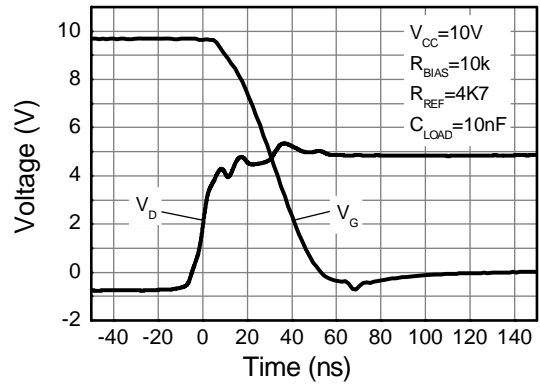
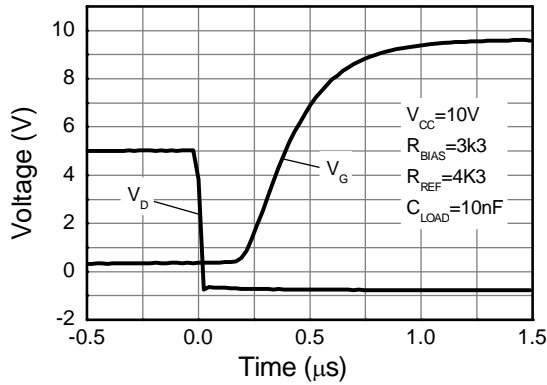


Supply Current vs Capacitive Load



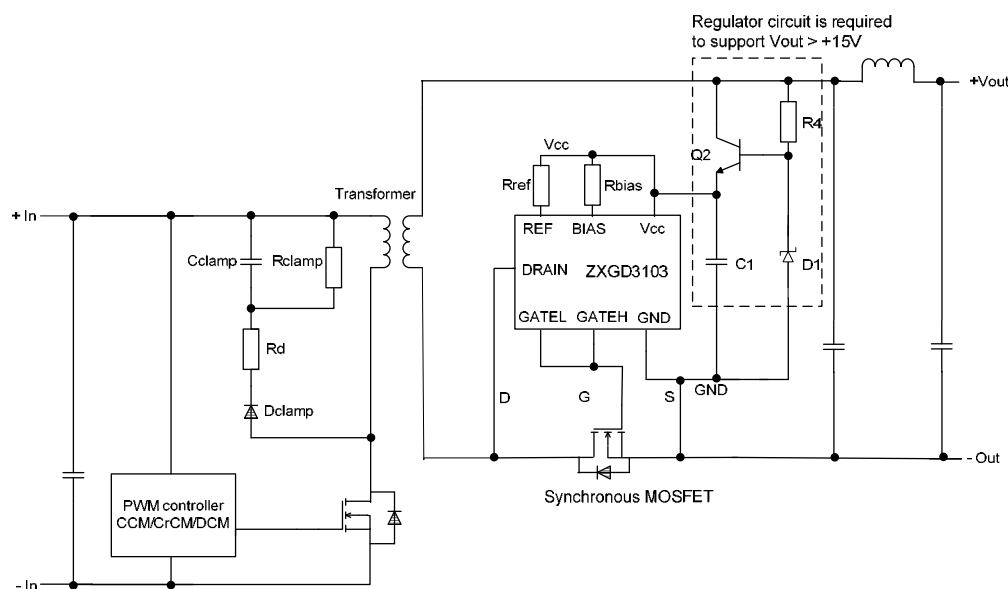
Gate Current vs Capacitive Load

## Typical Characteristics

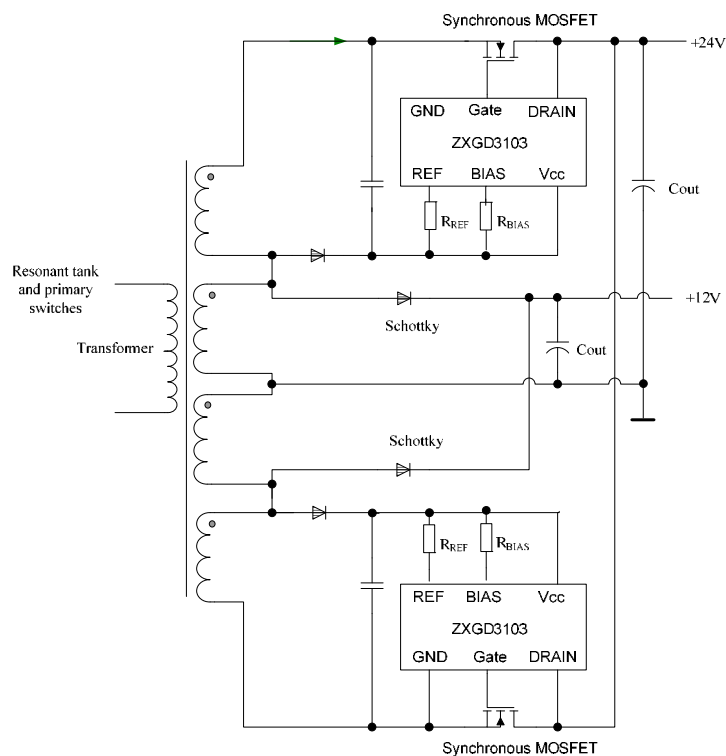


## Application information

The purpose of the ZXGD3103 is to drive a MOSFET as a low- $V_F$  Schottky diode replacement in offline power converters. When combined with a low  $R_{DS(ON)}$  MOSFET, it can yield significant power efficiency improvement, whilst maintaining design simplicity and incurring minimal component count. Figure 1 and 2 show typical configuration of ZXGD3103 for synchronous rectification in a Flyback and a multiple output resonant converter.



**Figure 1. Example connections in Flyback supply**



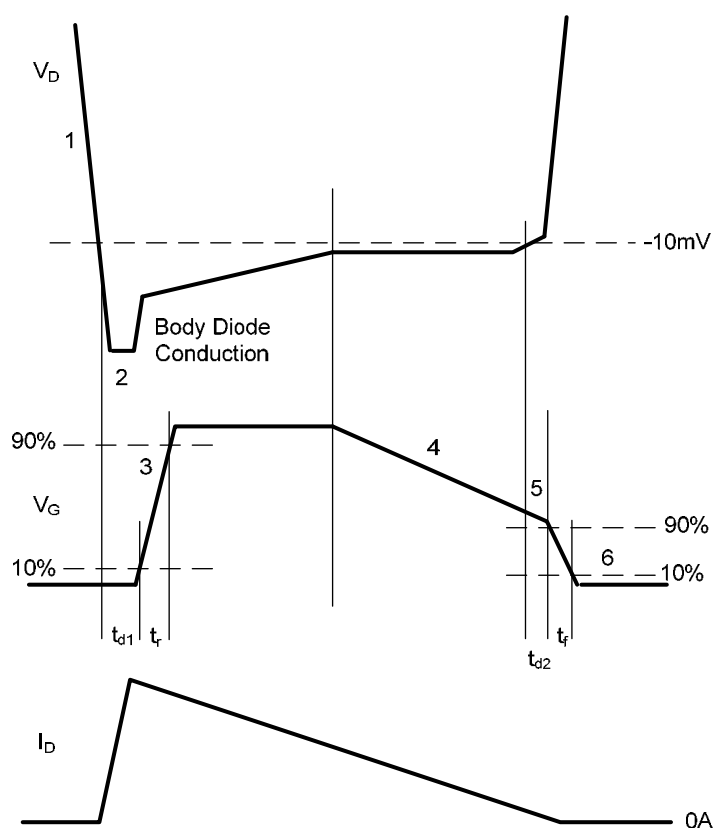
**Figure 2. Example connections in LLC supply**

## Descriptions of the normal operation

The operation of the device is described step-by-step with reference to the timing diagram in Figure 3.

1. The detector monitors the MOSFET Drain-Source voltage.
2. When, due to transformer action, the MOSFET body diode is forced to conduct there is approximately -0.8V on the Drain pin.
3. The detector outputs a positive voltage with respect to ground, this voltage is then fed to the MOSFET driver stage and current is sourced out of the GATE pin.
4. The controller goes into proportional gate drive control — the GATE output voltage is proportional to the on-resistance-induced Drain-Source voltage drop across the MOSFET. Proportional gate drive ensures that MOSFET conducts for majority of the conduction cycle and minimizes body diode conduction time.
5. As the Drain current decays linearly toward zero, proportional gate drive control reduces the Gate voltage so the MOSFET can be turned off rapidly at zero current crossing. The GATE voltage is removed when the Drain-Source voltage crosses the detection threshold voltage to minimize reverse current flow.
6. At zero Drain current, the controller GATE output voltage is pulled low to  $V_{G(off)}$  to ensure that the MOSFET is off.

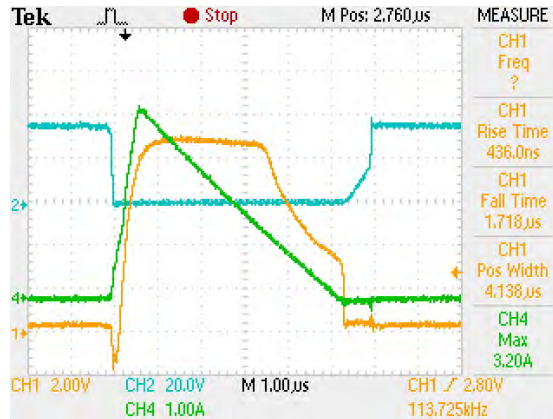
Figure 4 shows typical operating waveforms for ZXGD3103 driving a MOSFET with  $Q_{g(TOT)} = 82\text{nC}$  in a Flyback converter operating in critical conduction mode.



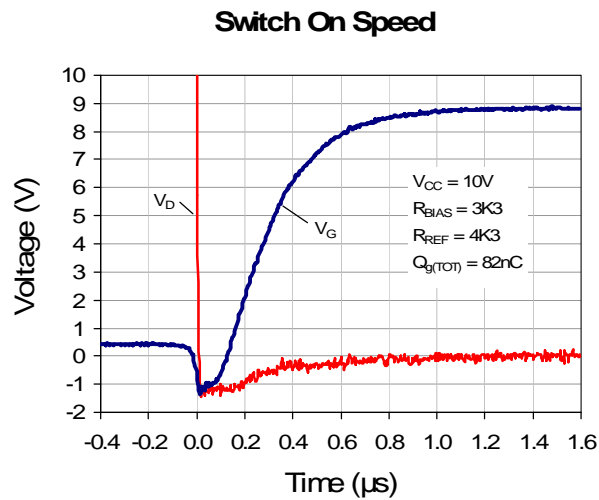
**Figure 3. Timing diagram for a critical conduction mode Flyback converter**



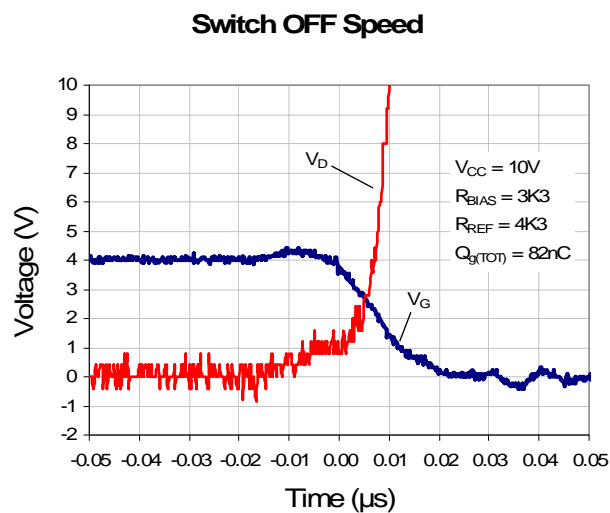
## Typical waveforms



**Fig 4a: Critical conduction mode**



**Fig 4b: Typical switch ON speed when driving a  $Q_{g(TOT)} = 82\text{nC}$  MOSFET**



**Fig 4c: Typical switch OFF speed when driving a  $Q_{g(TOT)} = 82\text{nC}$  MOSFET**

## Design considerations

It is advisable to decouple the ZXGD3103 closely to  $V_{CC}$  and ground due to the possibility of high peak gate currents with a 1 $\mu$ F X7R type ceramic capacitor as shown in Figure 2. The Gate pins should be as close to the MOSFET's gate as possible. Also the ground return loop should be as short as possible.

To minimize parasitic inductance-induced premature turn-off issue of the synchronous controller always keep the PCB track length between ZXGD3101's Drain input and MOSFET's Drain to less than 10mm. Low internal inductance MOSFET packages such as SO-8 and PolarPak are also recommended for high switching frequency power conversion to minimize body diode conduction.

R1, Q1 D1 and C1 in Figure 1 are only required as a series drop-down regulator to maintain a stable  $V_{CC}$  around 10V from a power supply output voltage greater than 15V.

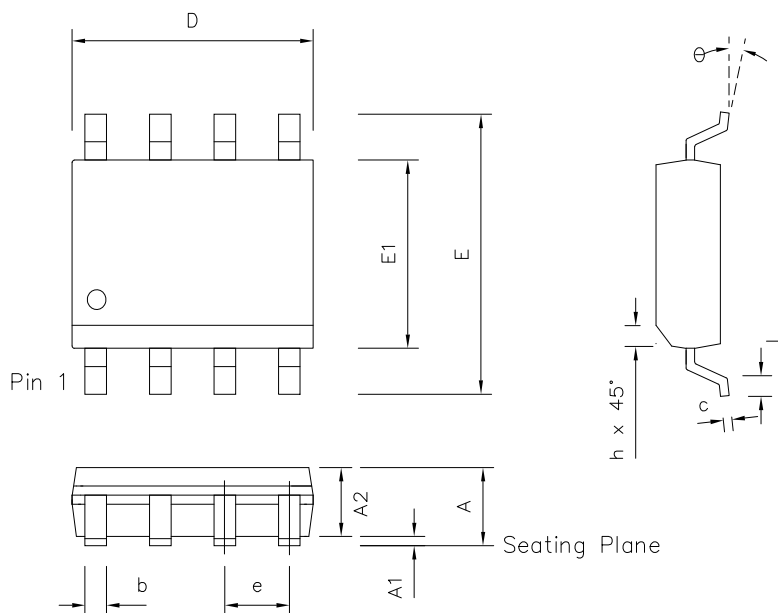
External gate resistors are optional. They can be inserted to control the rise and fall time which may help with EMI issues.

The proper selection of external resistors  $R_{REF}$  and  $R_{BIAS}$  is important to the optimum device operation. Select a value for resistor  $R_{REF}$  and  $R_{BIAS}$  from Table 1 based on the desired  $V_{CC}$  value. This provides the typical ZXGD3103's detection threshold voltage of 10mV.

**Table 1. Recommended resistor values for various supply voltages**

$V_{CC}$	$R_{BIAS}$	$R_{REF}$
5V	1K6	2K0
10V	3K3	4K3
12V	3K9	5K1
15V	5K1	6K8

## Package Outline and Dimensions



	Min mm	Max mm
A	—	1.75
A1	0.08	0.25
A2	1.30	1.50
D	4.80	5.30
E	5.79	6.20
E1	3.70	4.10
L	0.38	1.27
e	1.27 TYP	
b	0.30	0.50
O	0°	8°
h	—	0.35
All dimensions in mm		

#### **IMPORTANT NOTICE**

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel.

Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

#### **LIFE SUPPORT**

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

A. Life support devices or systems are devices or systems which:

1. are intended to implant into the body, or
2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.

B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2011, Diodes Incorporated

[www.diodes.com](http://www.diodes.com)



**Стандарт  
Электрон  
Связь**

Мы молодая и активно развивающаяся компания в области поставок электронных компонентов. Мы поставляем электронные компоненты отечественного и импортного производства напрямую от производителей и с крупнейших складов мира.

Благодаря сотрудничеству с мировыми поставщиками мы осуществляем комплексные и плановые поставки широчайшего спектра электронных компонентов.

Собственная эффективная логистика и склад в обеспечивает надежную поставку продукции в точно указанные сроки по всей России.

Мы осуществляем техническую поддержку нашим клиентам и предпродажную проверку качества продукции. На все поставляемые продукты мы предоставляем гарантию .

Осуществляем поставки продукции под контролем ВП МО РФ на предприятия военно-промышленного комплекса России , а также работаем в рамках 275 ФЗ с открытием отдельных счетов в уполномоченном банке. Система менеджмента качества компании соответствует требованиям ГОСТ ISO 9001.

Минимальные сроки поставки, гибкие цены, неограниченный ассортимент и индивидуальный подход к клиентам являются основой для выстраивания долгосрочного и эффективного сотрудничества с предприятиями радиоэлектронной промышленности, предприятиями ВПК и научно-исследовательскими институтами России.

С нами вы становитесь еще успешнее!

**Наши контакты:**

**Телефон:** +7 812 627 14 35

**Электронная почта:** [sales@st-electron.ru](mailto:sales@st-electron.ru)

**Адрес:** 198099, Санкт-Петербург,  
Промышленная ул, дом № 19, литера Н,  
помещение 100-Н Офис 331